JEITA: —
JEDEC: —
TERMINAL CONNECTER
①: EMITTER
②: COLLECTOR
③: BASE

查询"2SA1602A"供应商

2SA1235A 2SA1602A 2SA1993

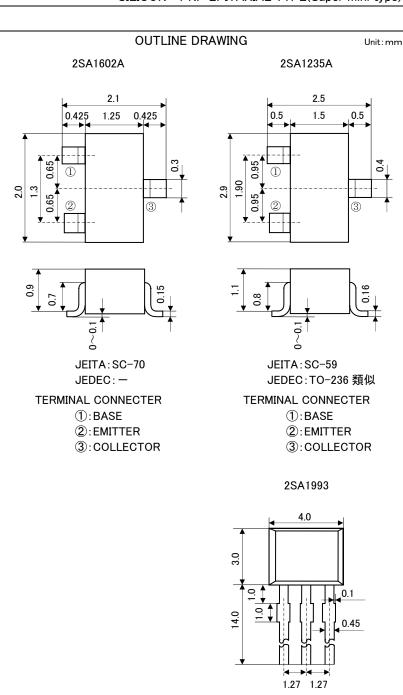
FOR LOW FREQUENCY AMPLIFY APPLICATION SILICON PNP EPITAXIAL TYPE(Super mini type)

FEATURE

- Super mini package for easy mounting
- *Excellent linearity of DC forward gain
- •Small collector to emitter saturation voltage VCE(sat)=-0.3V max

APPLICATION

For Hybrid IC,small type machine low frequency voltageAmplify application



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MAXIMUM RATINGS(Ta=25°C)

| Symbol | Parameter | Ratings | | | |
|------------------|---------------------------|-------------------|----------|---------|------|
| | Parameter | 2SA1235A | 2SA1602A | 2SA1993 | Unit |
| V _{CBO} | Collector to Base voltage | -60 | -60 | -50 | ٧ |
| V _{EBO} | Emitter to Base voltage | -6 | | | ٧ |
| V _{CEO} | Collector to Emitter | -50 | | | |
| | voltage | | | | |
| Ιc | Collector current | 200 | | | mA |
| Pc | Collector dissipation | 200 | 200 | 450 | mW |
| Tj | Junction temperature | +150 | | | °C |
| Tstg | Storage temperature | −55 ~ +150 | | | °C |

ELECTRICAL CHARACTERISTICS (Ta=25°C)

| Parame | Countries Total conditions | | | | Limits | | Unit |
|-------------------|------------------------------|--|--|-----|--------|------|------|
| ter | Symbol | Test conditions | | Min | Тур | Max | Unit |
| $V_{(BR)CEO}$ | C to E break down voltage | I _C =-100 μ A, R _{BE} =∞ | | -50 | | | V |
| I _{CBO} | Collector cut off current | 2SA1993 | V_{CB} =-50V, I $_{E}$ =0 | | | -0.1 | μΑ |
| | Emitter cut off current | 2SA1235A,2SA1602A | V_{CB} =-60V, I _E =0 | | | -0.1 | |
| I _{EBO} | DC forward current gain | V_{EB} =-6V, I $_{C}$ =0 | | | | -0.1 | μΑ |
| h _{FE} * | DC forward current gain | V_{CE} =-6V, I $_{C}$ =-1mA | | 150 | | 500 | _ |
| h _{FE} | C to E Saturation Vlotage | 2SA1993 | V _{CE} =-6V, I _C =-0.1mA | 50 | | | _ |
| | | 2SA1235A,2SA1602A | | 90 | | | _ |
| $V_{CE(sat)}$ | Gain bandwidth product | $I_{C} = -100 \text{mA}, I_{B} = -10 \text{mA}$ | | | | -0.3 | V |
| f _T | Collector output capacitance | V_{CE} =-6V, I_{E} =10mA | | | 200 | | MHz |
| Cob | C to E break down voltage | V_{CB} =-6V, I _E =0,f=1MHz | | | 4.0 | | pF |
| NF | Noise figure | V_{CE} =-6V, I _E =0.3mA,f=100Hz,RG=10k Ω | | | | 20 | dB |

*: It shows hFE classification in below table.

| | | Е | F |
|-----|----------|---------|---------|
| hFE | 2SA1235A | | |
| | 2SA1602A | 150~300 | 250~500 |
| | 2SA1993 | | |

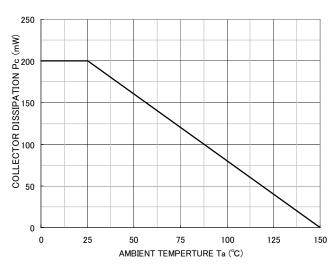
查询"2SA1602A"供应商

2SA1235A 2SA1602A 2SA1993

FOR LOW FREQUENCY AMPLIFY APPLICATION SILICON PNP EPITAXIAL TYPE(Super mini type)

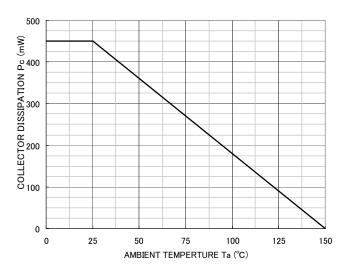
2SA1235A, 2SA1602

COLLECTOR DISSIPATION VS.AMBIENT TEMPERTURE



2SA1993

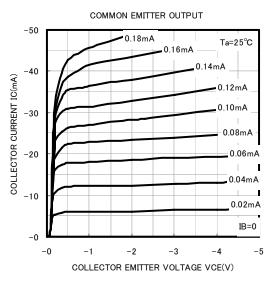
COLLECTOR DISSIPATION VS.AMBIENT TEMPERTURE

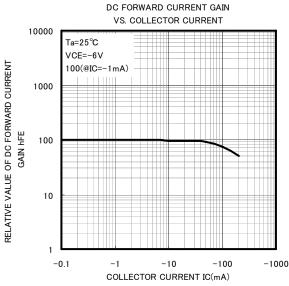


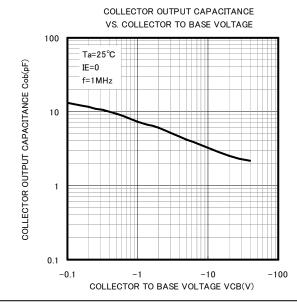
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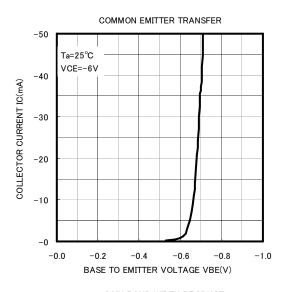
2SA1235A 2SA1602A 2SA1993

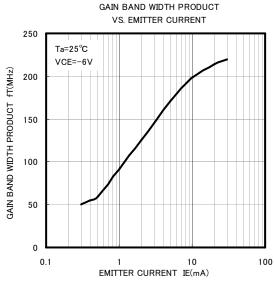
FOR LOW FREQUENCY AMPLIFY APPLICATION SILICON PNP EPITAXIAL TYPE(Super mini type)













Marketing division, Marketing planning department

6-41 Tsukuba, Isahaya, Nagasaki, 854-0065 Japan

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